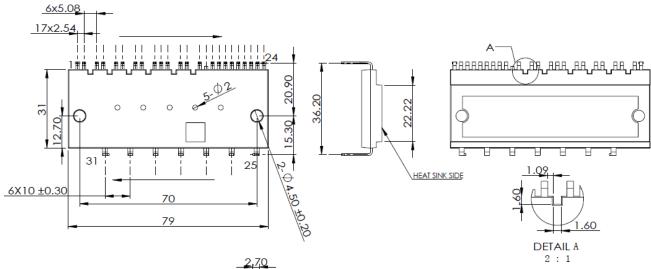
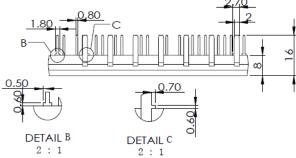


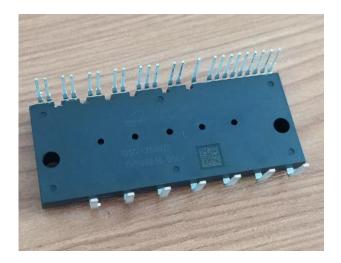
Compact - IPM ID50FFX60U2S

Features

- Adopt the latest trench IGBT technology to get a good overall loss trade-off.
- Open Emitter on N terminal for low cost current sensing application.
- Matched propagation delay and arm shooting through prevention.
- Built-in bootstrap diodes with current limiting resistor.
- Provided a fault signal (FO pin) and shut-off internal IGBT when suffer S.C. and under-voltage faulty event.
- RoHS compatible.
- UL 1557 Compliance.







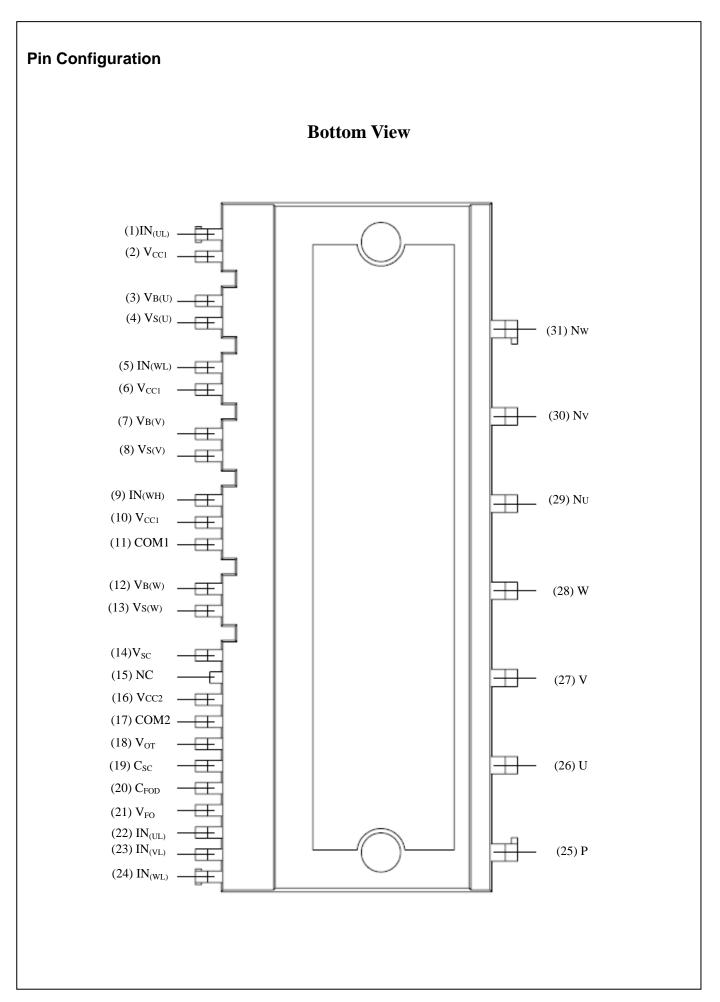
TERMINAL CODE

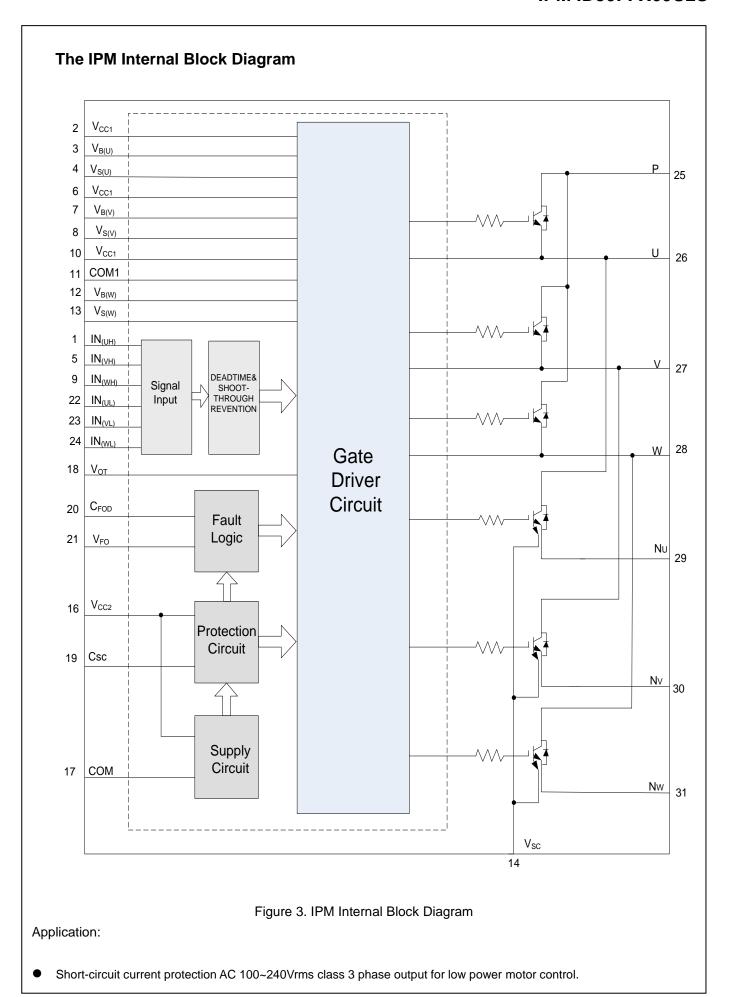
$1 \text{ IN}_{\text{(UH)}}$	17 COM2
2 V _{CC1}	18 V_{OT}
$3\;V_{B(U)}$	19 Csc
4 V _{S(U)}	$20~\mathrm{C}_\mathrm{FOD}$
5 IN _(VH)	$21~V_{FO}$
6 V _{CC1}	22 IN _(uL)
$7 V_{B(V))}$	23 IN _(vL)
8 V _{S(V)}	24 IN(wL)
9 IN _(WH)	25 P
10 Vcc ₁	26 U
11 COM1	27 V
12 V _{B(W))}	28 W
13 V _{S(W))}	$29\;N_{U}$
14 V _{SC}	$30 N_{\rm V}$
15 NC	$31 N_{\rm W}$
16 V _{CC2}	

Table1: Pin Descriptions

No.	Symbol	Pin Description
1	IN _(UH)	Signal Input Terminal for High-side U Phase
2	Vcc1	Supply Voltage Terminal for Driver IC
3	$V_{B(U)}$	High - side Bias Voltage for U Phase IGBT Driving
4	V _{S(U)}	High - side Bias Voltage Ground for U Phase IGBT Driving
5	IN _(VH)	Signal Input Terminal for High-side V Phase
6	Vcc1	Supply Voltage Terminal for Driver IC
7	$V_{B(V)}$	High - side Bias Voltage for V Phase IGBT Driving
8	V _{S(V)}	High - side Bias Voltage Ground for V Phase IGBT Driving
9	IN _(WH)	Signal Input Terminal for High-side W Phase
10	V _{CC1}	Supply Voltage Terminal for Driver IC
11	COM1	Reference Voltage Terminal for Driver IC
12	V _{B(W)}	High - side Bias Voltage for W Phase IGBT Driving
13	V _{S(W)}	High - side Bias Voltage Ground for W Phase IGBT Driving
14	V _{SC}	Current sensing input voltage
15	NC	No connection
16	V _{CC2}	Supply Voltage Terminal for Driver IC
17	COM2	Reference Voltage Terminal for Driver IC
18	Vот	Temperature Output Terminal
19	Csc	Capacitor (Low-pass Filter) for Short-Current Detection Input
20	C_FOD	Capacitor for Fault Output Duration Time Selection
21	V _{FO}	Fault Output Terminal
22	IN _(UL)	Signal Input Terminal for Low-side U Phase
23	IN _(VL)	Signal Input Terminal for Low-side V Phase
24	IN _(WL)	Signal Input Terminal for Low-side W Phase
25	Р	Positive DC – Link Input
26	U	Output Terminal for U Phase
27	V	Output Terminal for V Phase
28	W	Output Terminal for W Phase
29	Nυ	Negative DC-Link Input Terminal for U Phase
30	N _V	Negative DC-Link Input Terminal for V Phase
31	Nw	Negative DC-Link Input Terminal for W Phase

(see figure 2, next page)





MAXIMUM RATINGS $(T_j = 25^{\circ}C)$

INVERTER PART

Item	Symbol	Min.	Max.	Unit
Between collector to emitter voltage	V _{CES} (IGBT)	-	600	V
Supply voltage P-N	V _{PN}	-	450	V
Supply voltage (surge) P-N	VPN (surge)	-	500	V
Each IGBT collector current	± Ic (Tc = 25℃)	-	20	Α
Each IGBT collector current (peak)	$\pm I_{CP}$ (Tc = 25°C, pulse)	-	60	Α
Collector dissipation	Pc (Tc = 25° C, per one chip)	-	70	W
Junction temperature	Tj (Note 1)	-40	+150	$^{\circ}$

Note 1: Power chip in IPM is qualified for 150°C operation. But overall junction temperature should be limited by $T_j \le 125$ °C (@ $T_c \le 100$ °C) to fit long term reliability requirement.

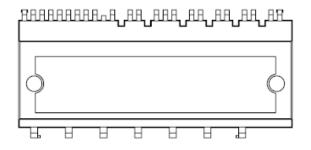
CONTROL PART

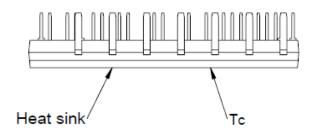
Item	Symbol	Min.	Max.	Unit
Driver IC supply voltage	Vcc	-0.3	20	V
P - side floating supply voltage	$V_{B(u)S(u), B(V)S(V), B(W)S(W)}$	-0.3	20	V
Current sensing input voltage	V _{SC}	-0.3	Vcc+0.3	V
Logic input voltage	$\begin{split} &IN_{(UH)}, IN_{(VH)}, IN_{(WH)}, \\ &IN_{(UL)}, IN_{(VL)}, IN_{(WL)} \end{split}$	-0.3	Vcc+0.3	V
Fault output voltage	VFO	-0.3	Vcc+0.3	V
Fault output current	IFO	-	10	mA

TOTAL SYSTEM

Item	Sy	mbol	Min.	Max.	Unit
Module case operating temperature	Tc	(Note 2)	-20	+100	$^{\circ}\mathbb{C}$
Storage temperature	T _{stg}		-40	+125	$^{\circ}\mathbb{C}$
Isolation voltage (60Hz Sinusoidal, AC 1 minute, pins to heat-sink plate)	V _{iso}		-	2500	Vrms

Control terminal





Power terminal

Figure 4. Tc Measurement Point

THERMAL RESISTANCE

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Junction to case thermal	R _{th(j-c)Q}	IGBT part (1/6)	-	0.78		°C 111
resistance	R _{th(j-c)} F	FWD part (1/6)	-	1.4		°C/W

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

INVERTER PART

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Collector-emitter saturation voltage	VCE (sat)	$V_{CC} = V_{B(U)S(U), B(V)S(V), B(W)S(W)} = 15V, I_{C} = 15, V_{SC} = 0V$		1.5		>
FWD forward voltage drop	VF	$T_j = 25$ °C, - $I_C = 20$ A		1.5		V
Switching times	T_{on}			1.5		
	Tr	$V_D = 300V$,		0.3		μS
	$T_{c(on)}$	$V_{CC} = V_{B(U)S(U), B(V)S(V), B(W)S(W)} = 15V,$		0.4		
(Fig. 5)	T_{off}	$I_C = 20A, T_j = 25^{\circ}C,$		3		
(i ig. 3)	T _f	$V_{IN} = 5V <> 0V,$		0.15		
	$T_{c(off)}$	V _{SC} = 0V, Inductive Load		0.4		
	T_{rr}			0.25		
Collector-emitter cut-off current	I _{CES}	V _{CE} =V _{CES}			500	μA

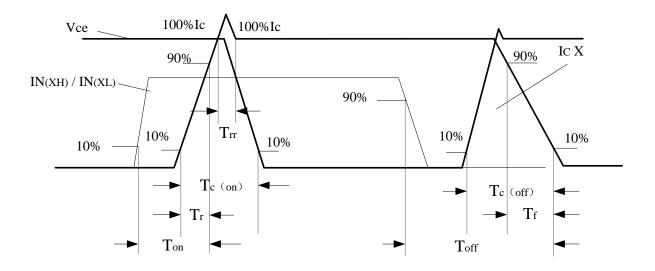


Figure 5. Switching Time Definition

CONTROL PART $(T_j = 25^{\circ}C)$

Item	Item Symbol		Min.	Тур.	Max.	Unit
IN(uh. vh. wh), IN(ul. vl. wl) ON threshold voltage	$V_{\text{th(on)}}$		1.4	1.7	2.0	V
IN _(UH, VH, WH) ,IN _(UL, VL, WL) OFF threshold voltage	$V_{th(off)}$		2.2	2.5	2.8	V
IN _(UH, VH, WH) input bias current	In(uh. vh. wh)(hi)	$V_{IN(UH, VH, WH)} = 5V$	-	-	220	μA
IN(UH, VH, WH) INPUT DIAS CUITEIT	In(uh. vh. wh) (lo)	$V_{IN(UH, VH, WH)} = 0V$	-	-	300	μΑ
IN(UL, VL, WL) input bias current	I _{IN(UL, VL, WL)} (HI)	$V_{IN(UL, VL, WL)} = 5V$	-	-	220	
IN(OL. VL. WL) Input bias current	IN(UL, VL, WL) (LO)	$V_{IN(UL, VL, WL)} = 0V$	-	-	300	μΑ
Short circuit trip level	Isc	Rs=40.2, not connecting external shut resistor		90		Α
Driver IC supply voltage	Vcc		13.5	15.0	16.5	V
P - side floating supply voltage	$V_{B(U)S(U),\;B(V)S(V),\;B(W)S(W)}$		13.5	15.0	16.5	V
Vcc terminal input current	lc		-	-	2.3	mA
Foult output voltage	V _{FOH}	V _{SC} =0V (Note 2)	4.9	-	•	V
Fault output voltage	V _{FOL}	V _{SC} =1V	-	-	200	mV
Short circuit trip level	V _{SC(ref)}	V_{CC} =15 V , T_j = 25 $^{\circ}$ C	0.41	0.46	0.51	V
Fault output pulse width	t _{FOD}	(Note 3)	100		-	us
Supply sirguit under voltage	UVT _{VCC}	Trip level	8.6	9.4	10.2	V
Supply circuit under voltage	UVR _{VCC}	Reset level	9.6	10.4	11.2	V
protection	UVH	Hysteresis	-	1.0	•	V
IN(UL. VL. WL) Input filter time	tin,fil	VIN = 0 & 5V (Note 4)	100	200	-	ns

Note 2: V_{FO} output is open collector type, so this signal line should be pulled up to the +5V power supply with approximately 4.7K Ω

Note 3: Fault output pulse width is filter capacitor of S.C. depended.

Note 4: For high side PWM, IN(UH、VH、WH) pulse width must be ≥ 1 us.

Input Filter Function

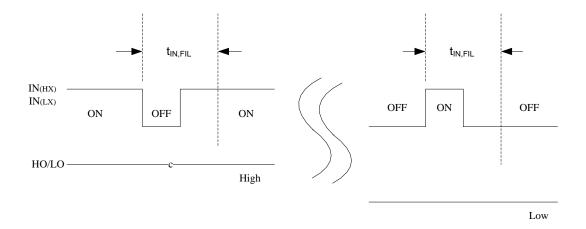


Figure 6. Input Filter Function

RECOMMENDED OPERATION CONDITIONS

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
DC – Link Supply voltage	V_D	Applied between P-N	0	400	450	V
Driver IC supply voltage	V _{CC}	Applied between V _{CC} - COM	13.5	15.0	16.5	V
P - side floating supply voltage	V_{BS}	Applied between $V_{B(u, v, w)} - V_{S(u, v, w)}$	13.5	15.0	16.5	V
Input ON threshold voltage	$V_{\text{sc}(\text{ON})}$	Applied between IN(UH, VH, WH) - COM		0 ~ 0.65		
Input OFF threshold voltage	$V_{\text{sc}(\text{OFF})}$	and IN _(UL, VL, WL) - COM		4.0 ~ 5.5		
Supply voltage ripple	ΔV_D , ΔV_{DB}		-1	-	1	V/µs
Arm shoot-through blocking time	t dead		2	-	-	μs
PWM input frequency	f _{РWМ}	Tc≦ 100°C, Tj≦ 125°C	-	15	-	kHz

MECHANICAL CHARACTERISTICS AND RATINGS

Item	Condition			Тур.	Max.	Unit
Mounting torque	Mounting screw: M3	Recommended 0.65N•m	0.60	0.65	0.70	N•m
Weight			-	69	-	g
Heat-sink flatness			-50	•	100	μm

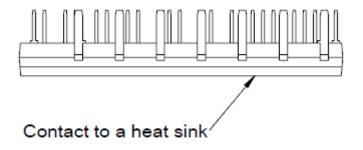
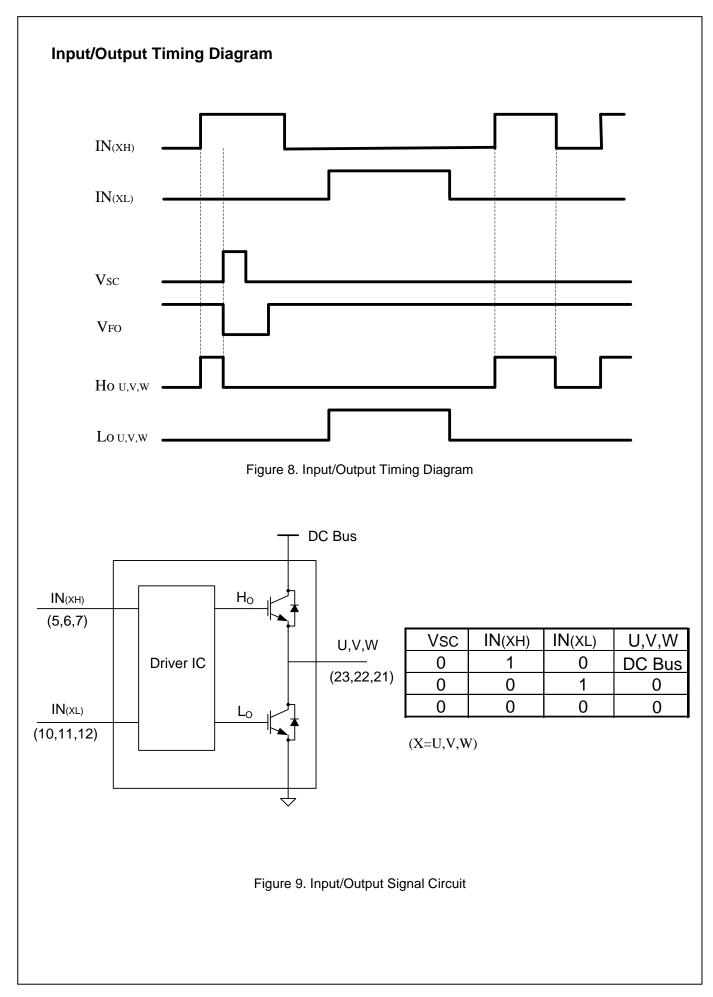


Figure 7. Measurement Location of Heat-sink Flatness



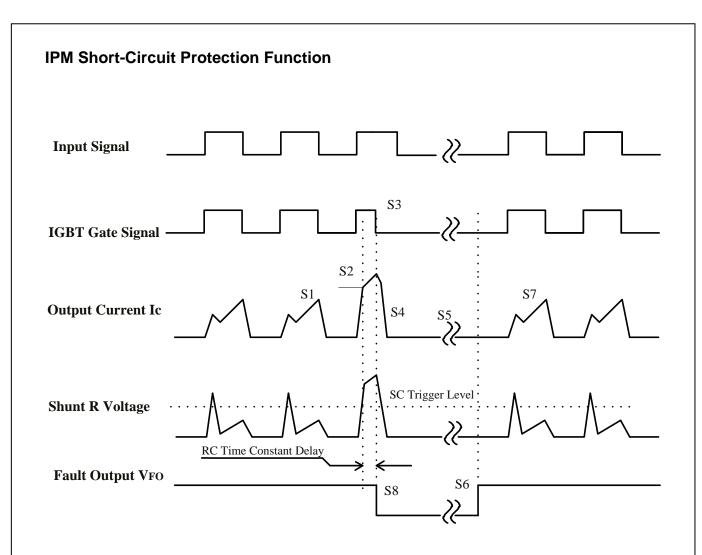


Figure 10. Timing Chart of SC Operation

- S1. The IGBT's are controlled by input PWM signal.(Normal operation)
- S2. Short circuit event occur and reach the limited level. (SC protection is trigger).
- S3. IGBT gate driving signal is disabled.
- S4. Current is cut off caused by IGBT turns OFF.
- S5. Disabled state
- S6. Fault level is kept on low level during the fault output activation
- S7. IGBT returns for normal operation when fault state is reset
- S8. Fault output starting once SC protection is trigger.

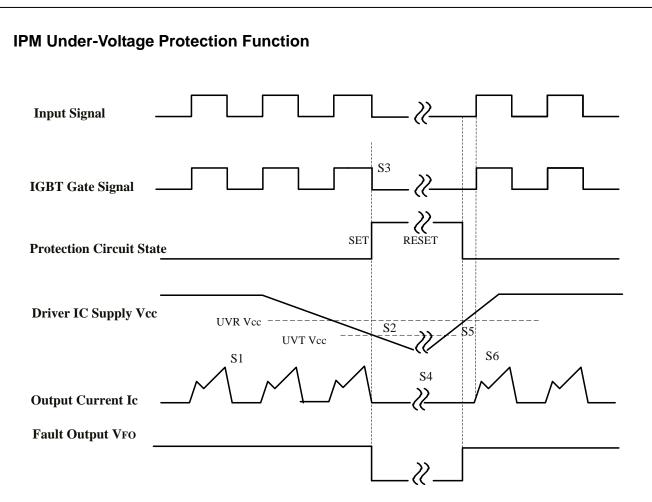


Figure 11. Timing Chart of Under-Voltage Operation

- S1. The IGBT's are controlled by input PWM signal.(Normal operation)
- S2. Under-voltage protection is trigger
- S3. IGBT driving signals are disabled when fault condition occur
- S4. Fault state and the period will be able to control by external capacitor value.
- S5. Under-voltage event is recovered
- S6. IGBT returns for normal operation when fault state is reset

Direct Input (without Photo Coupler) Interface Example

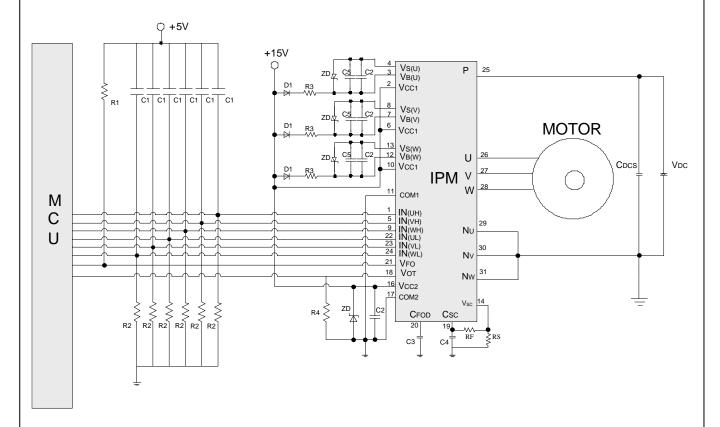


Figure 12. Typical Application Circuit Interface Example without Photo-Coupler

Design reference:

- 1. $R1:100\Omega$
- 2. R2: $4.7 \sim 10 \text{K}\Omega$ (VFO output is open collector so to have a pull high resistor is needed.)
- 3. C1: $10 \sim 100 \mu F$ (Electrolytic, low impendence)
- 4. C2: 100 ~ 1000pF (Ceramic) (The capacitor could filter the noise, but should be careful to the dead time)
- 5. C4: 22nF ~ 44nF (Ceramic)
- 6. C8: 220µF (Electrolytic, low impendence)
- 7. D1: Zener diode (It is recommended to insert a Zener diode to prevent gate lifting and surge destruction)
- 8. Only connect either pin 9 or pin 16 to ground, do not connect both together to form the ground loop internally.

Current Sense Shceme

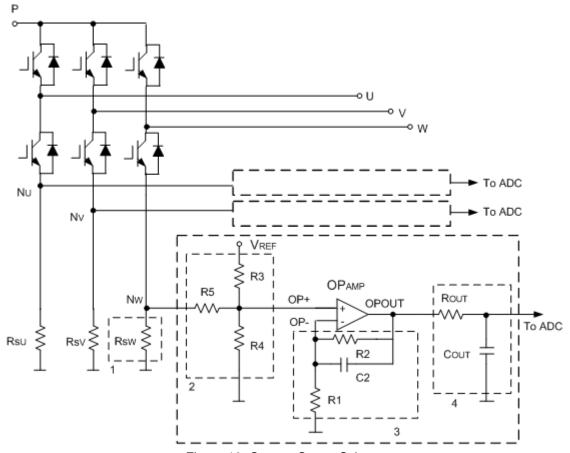


Figure 13. Current Sense Scheme

Description:

- 1. Half-bridge current sensing
- 2. Voltage shifting of the V_{sense}
- 3. Voltage gain and filtering
- 4. Capacitor required by the ADC for sampling purpose

Rout resistor is usually required in order to make the OPAMP stable when the Cout capacitance increases

Design Reference:

1. R1 : 1.0 $K\Omega$

2. R2 : 5.6 KΩ

3. R3 : 4.7 $\mbox{K}\Omega$

4. R4: 910 Ω

5. R5 : 910 Ω

 $6.ROUT:1.0\;K\Omega$

7. C2:10pF (Ceramic)

Precautions on Electrostatic Electricity

- (1) Operators must wear anti-static clothing and conductive shoes (or a leg or heel strap).
- (2) Operators must wear a wrist strap grounded to earth via a resistor of about 1 $M\Omega$.
- (3) Soldering irons must be grounded from iron tip to earth, and must be used only at low voltages.
- (4) If the tweezers you use are likely to touch the device terminals, use anti-static tweezers and in particular avoid metallic tweezers. If a charged device touches a low-resistance tool, rapid discharge can occur. When using vacuum tweezers, attach a conductive chucking pat to the tip, and connect it to a dedicated ground used especially for anti-static purposes (suggested resistance value: 10⁴ to 10⁸Ω).
- (5) Do not place devices or their containers near sources of strong electrical fields (such as above a CRT).
- (6) When storing printed circuit boards which have devices mounted on them, use a board container or bag that's protected against static charge. To avoid the occurrence of static charge or discharge due to friction, keep the boards separate from one other and do not stack them directly on top of one another.
- (7) Ensure, if possible, that any articles (such as clipboards) which are brought to any location where the level of static electricity must be closely controlled are constructed of anti-static materials.
- (8) In cases where the human body comes into direct contact with a device, be sure to wear anti-static finger covers or gloves (suggested resistance value: $10^8\Omega$ or less).
- (9) Equipment safety covers installed near devices should have resistance ratings of $10^9\Omega$ or less.
- (10) If a wrist strap cannot be used for some reason, and there is a possibility of imparting friction to devices, use an ionizer.

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